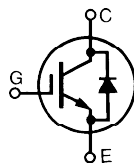


XPT™ 650V IGBT GenX4™ w/ Sonic Diode

IXXH40N65B4H1

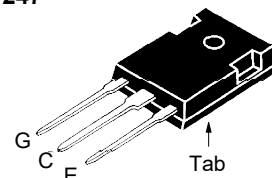
$V_{CES} = 650V$
 $I_{C110} = 40A$
 $V_{CE(sat)} \leq 2.0V$
 $t_{fi(typ)} = 40ns$



Extreme Light Punch Through
IGBT for 5-30 kHz Switching

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	650	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	123	A
I_{C110}	$T_C = 110^\circ C$	40	A
I_{F110}	$T_C = 110^\circ C$	40	A
I_{CM}	$T_C = 25^\circ C$, 1ms	225	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 10\Omega$	$I_{CM} = 80$	A
(RBSOA)	Clamped Inductive Load	@ $V_{CE} \leq V_{CES}$	
t_{sc}	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ C$	10	μs
(SCSOA)	$R_G = 82\Omega$, Non Repetitive		
P_C	$T_C = 25^\circ C$	455	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ C$
M_d	Mounting Torque	1.13/10	Nm/lb.in
Weight		6	g

TO-247



G = Gate C = Collector
 E = Emitter Tab = Collector

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Anti-Parallel Sonic Diode
- Avalanche Rated
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			25 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 40A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$	1.60	1.87	V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 40\text{A}, V_{CE} = 10\text{V}$, Note 1	14	23	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2110	pF
C_{oes}			200	pF
C_{res}			33	pF
$Q_{g(on)}$	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		66	nC
Q_{ge}			16	nC
Q_{gc}			27	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		19	ns
t_{ri}			48	ns
E_{on}			1.40	mJ
$t_{d(off)}$			112	ns
t_{fi}			40	ns
E_{off}			0.75	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		17	ns
t_{ri}			44	ns
E_{on}			2.20	mJ
$t_{d(off)}$			134	ns
t_{fi}			73	ns
E_{off}			1.40	mJ
R_{thJC}				0.33 $^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

Reverse Sonic Diode (FRD)

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 30\text{A}, V_{GE} = 0\text{V}$, Note 1			2.5 V
		$T_J = 150^\circ\text{C}$	2.15	V
I_{RM}	$I_F = 30\text{A}, V_{GE} = 0\text{V}, T_J = 150^\circ\text{C}$ $-di_F/dt = 500\text{A}/\mu\text{s}, V_R = 300\text{V}$		25	A
t_{rr}			120	ns
R_{thJC}				0.60 $^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

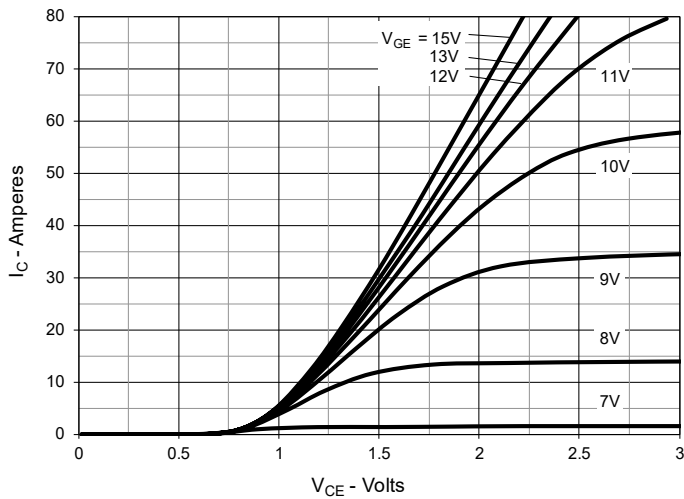
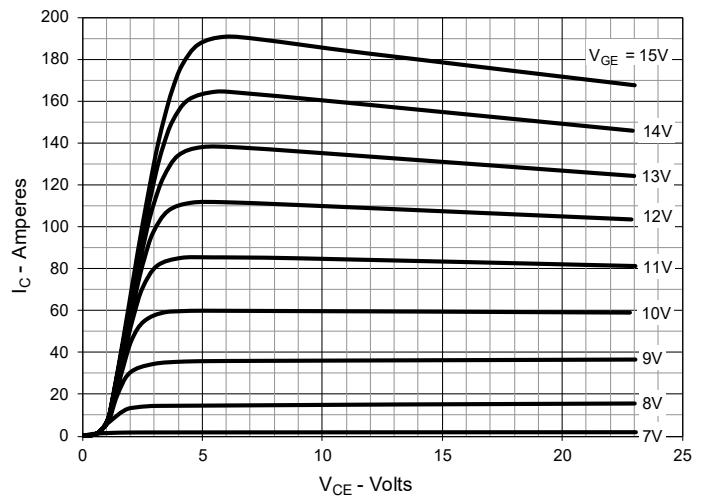
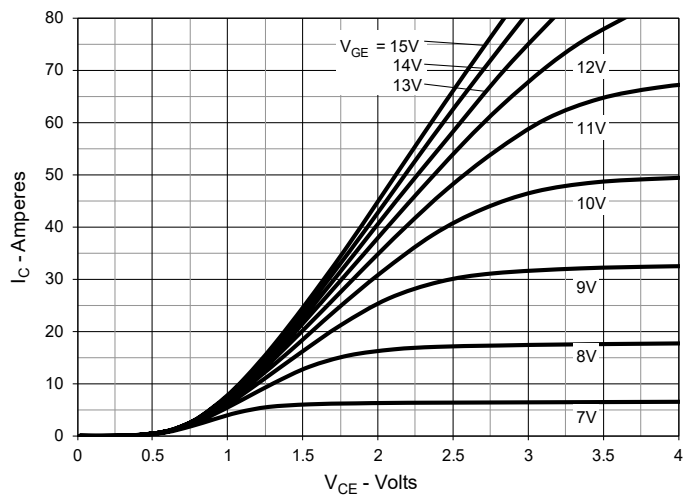
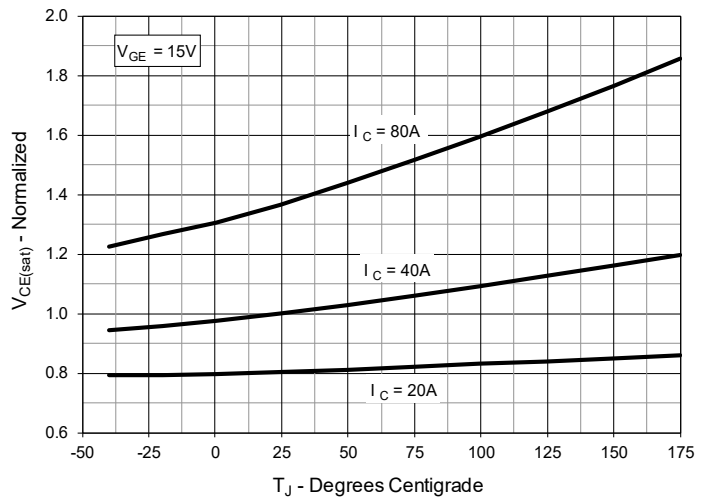
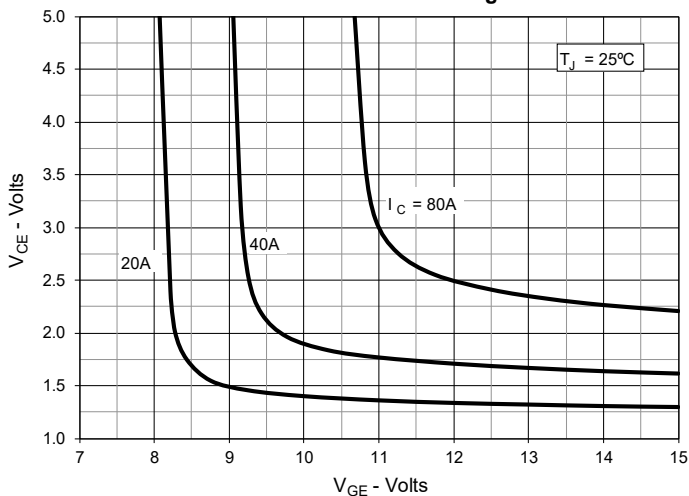
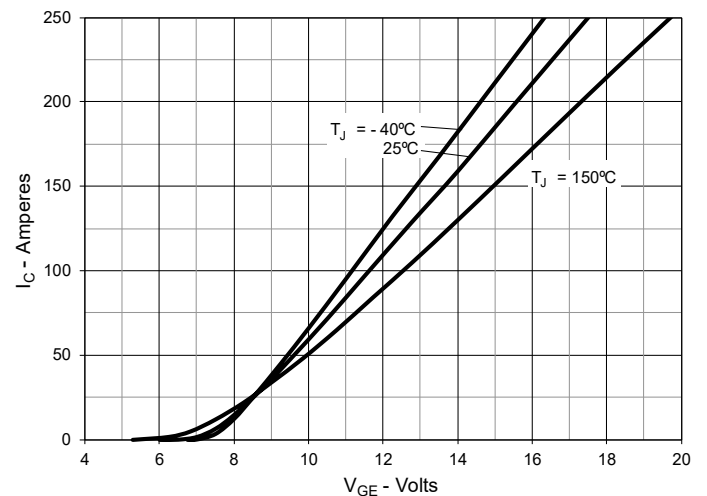
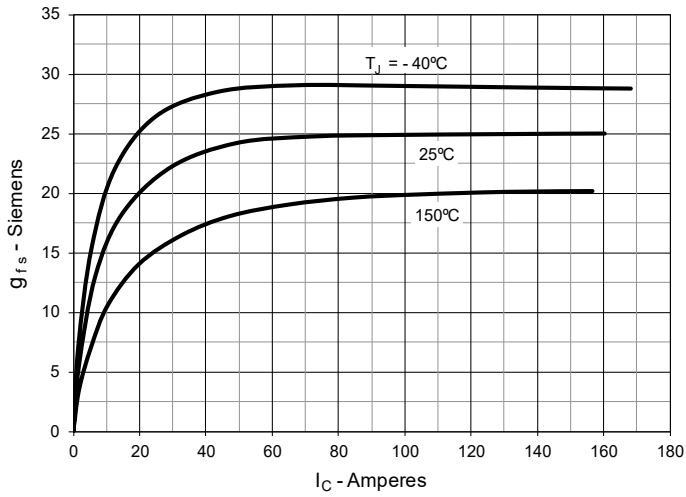
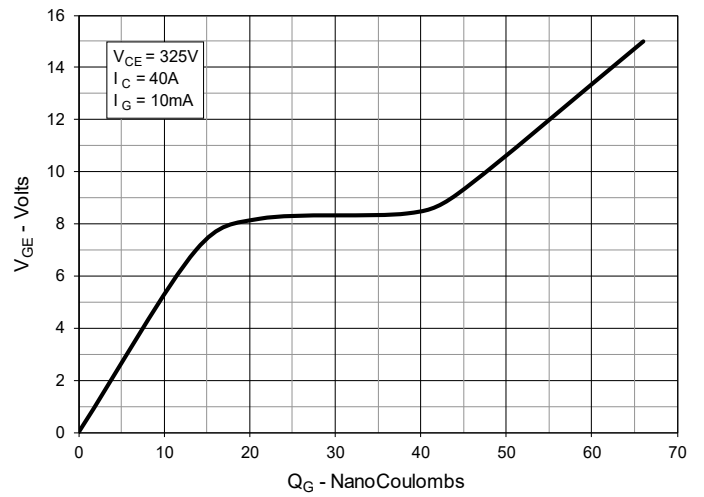
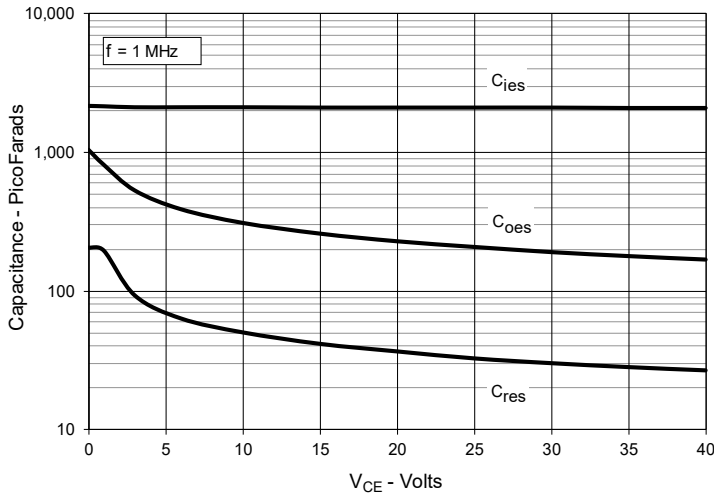
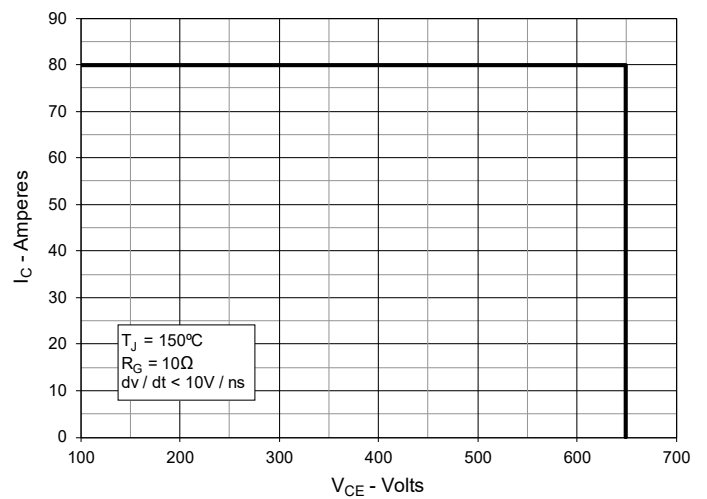
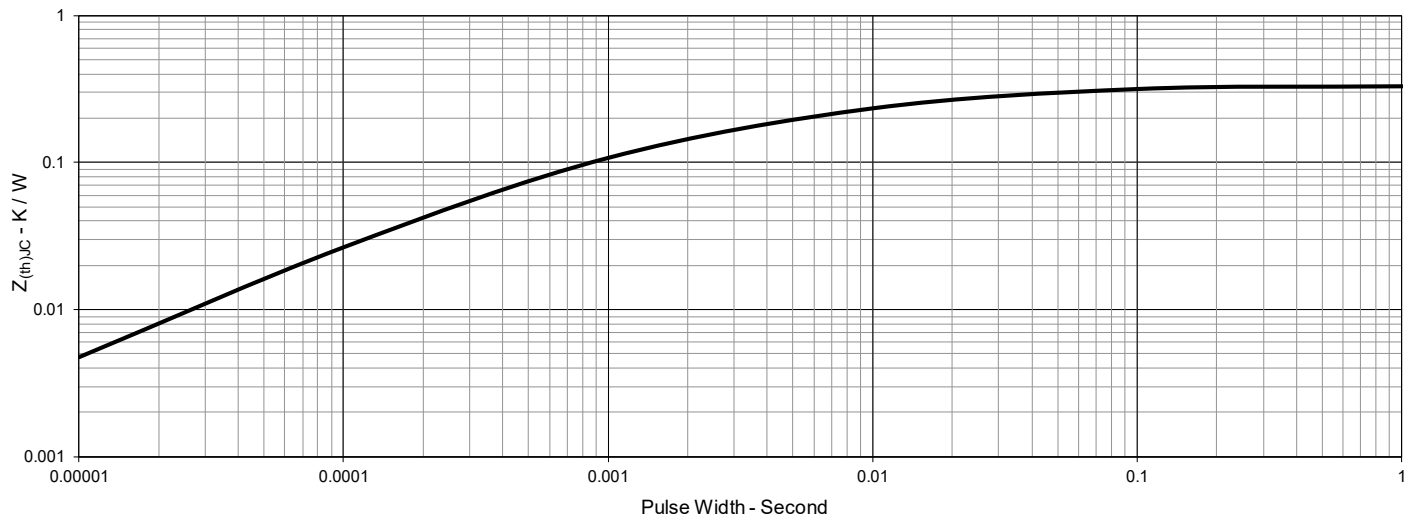
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance (IGBT)


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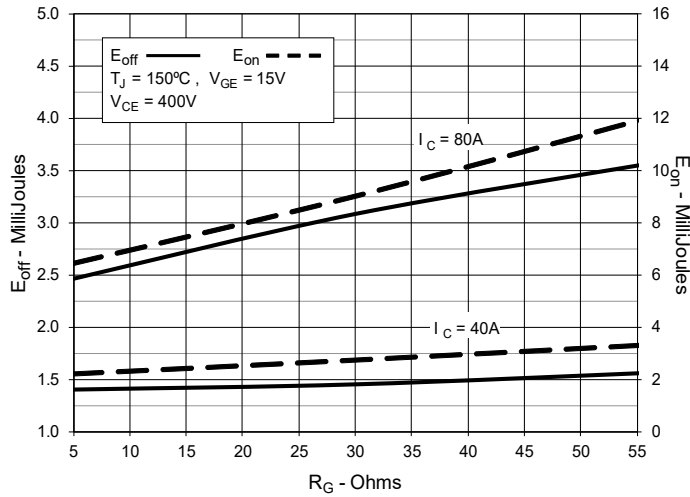
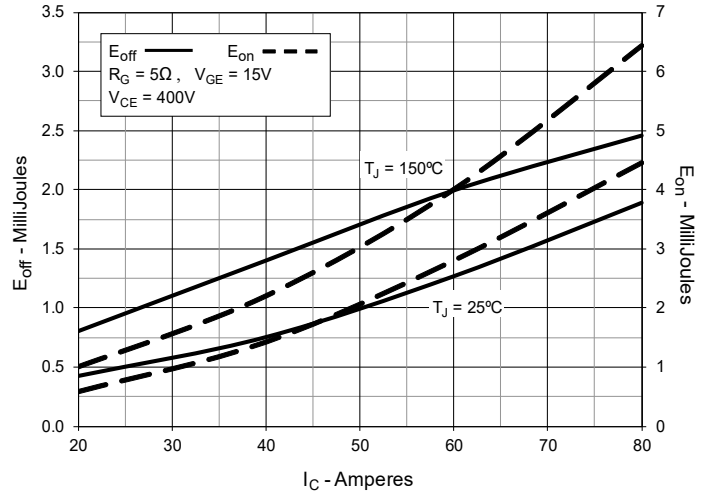
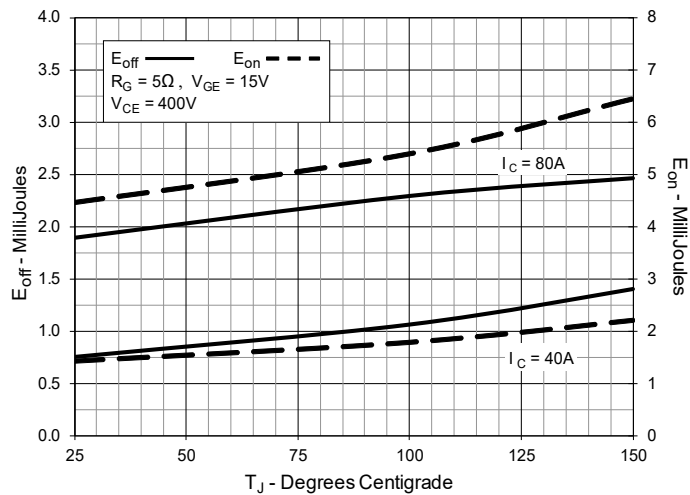
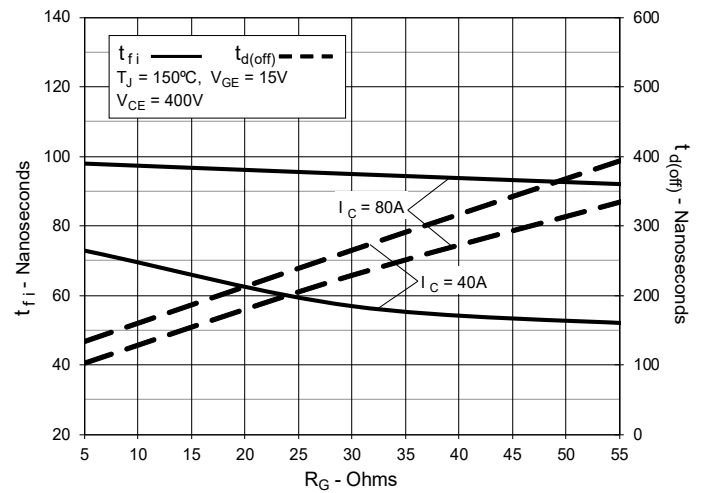
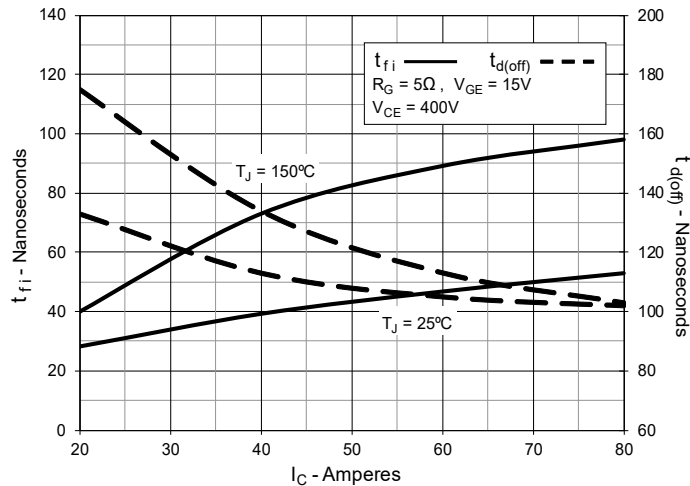
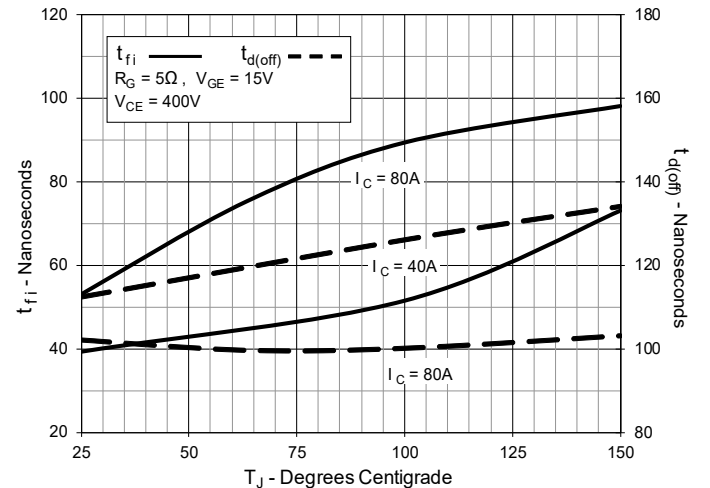
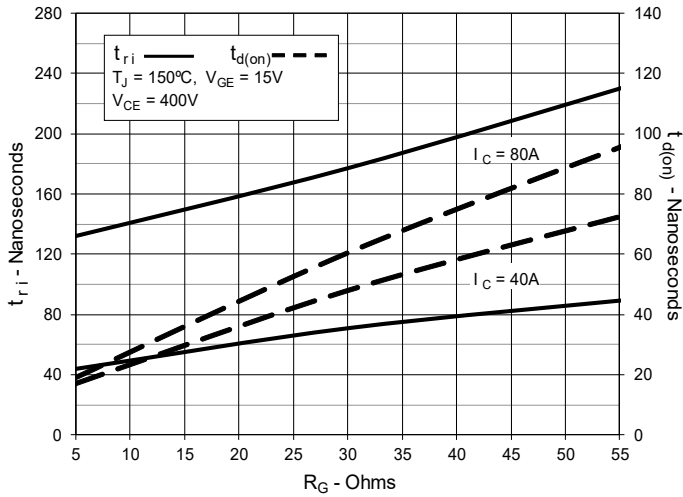
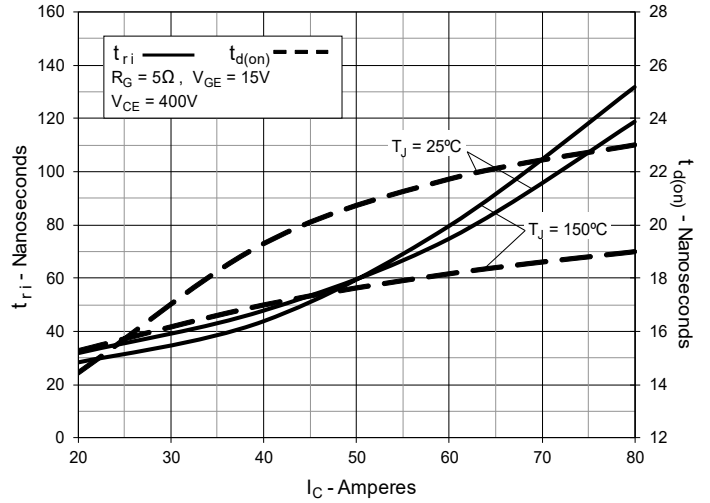
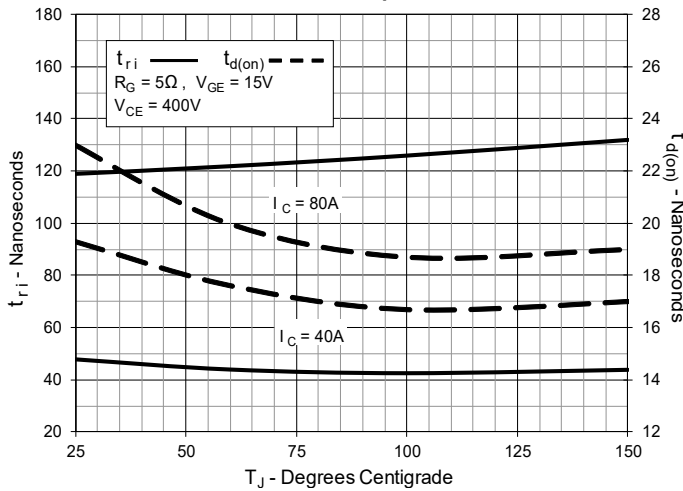
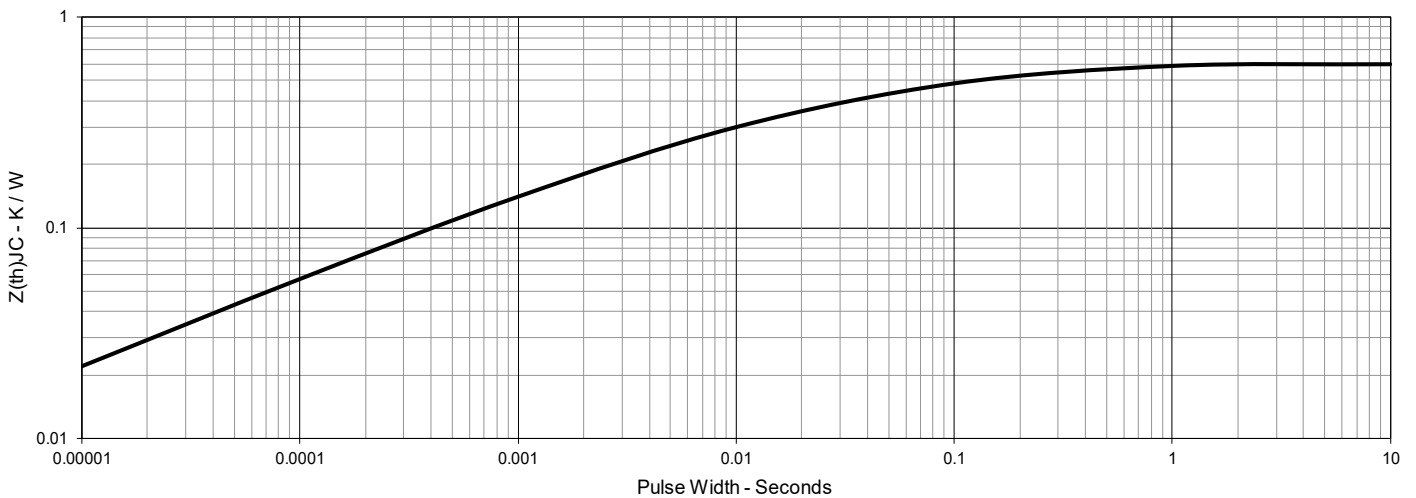
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

Fig. 21. Maximum Transient Thermal Impedance (Diode)


Littelfuse reserves the right to change limits, test conditions, and dimensions.

Fig. 22. Forward Current vs. Forward Voltage

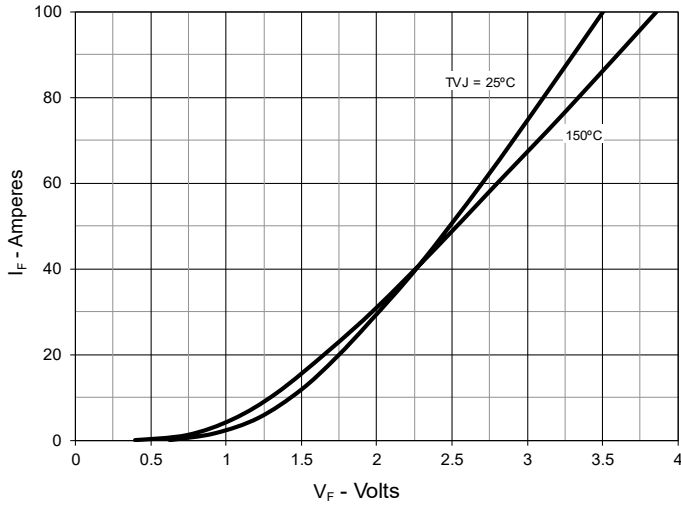


Fig. 23. Reverse Recovery Charge Q_{RR} vs. $-di_F/dt$

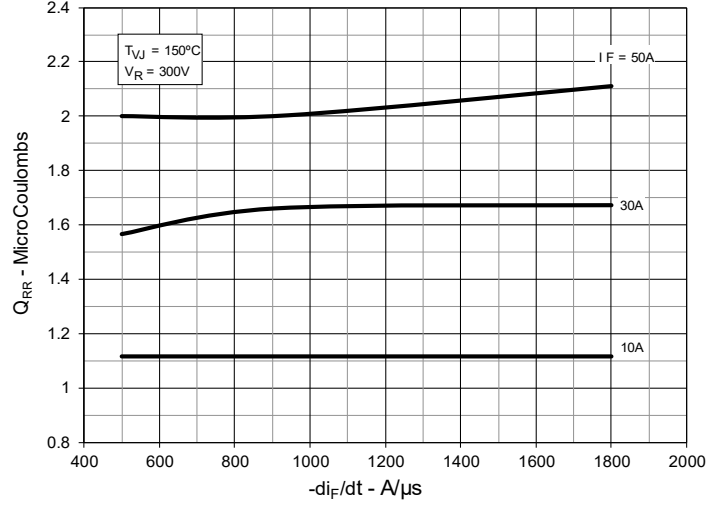


Fig. 24. Peak Reverse Current I_{RM} vs. $-di_F/dt$

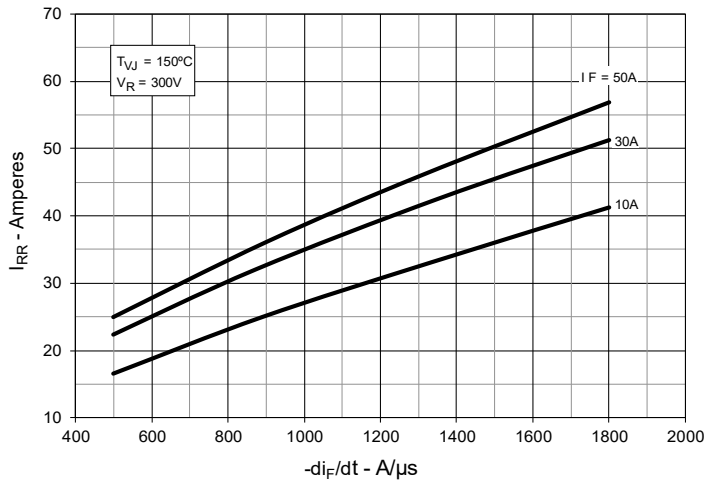


Fig. 25. Recover Time t_{RR} vs. $-di_F/dt$

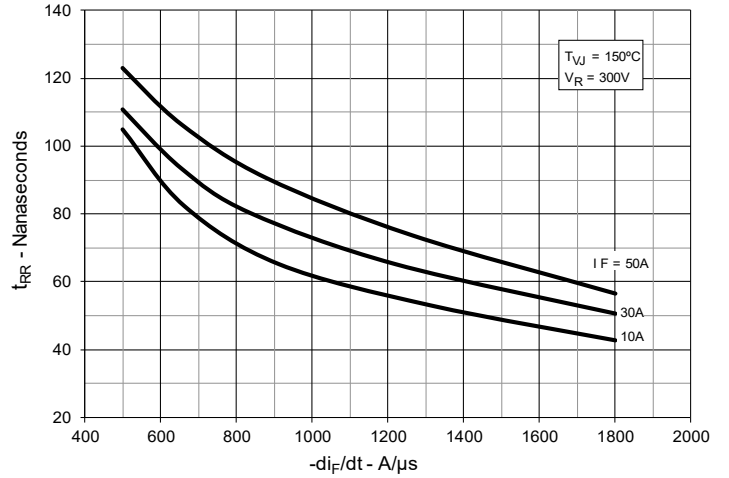


Fig. 26. Recovery Energy E_{REC} vs. $-di_F/dt$

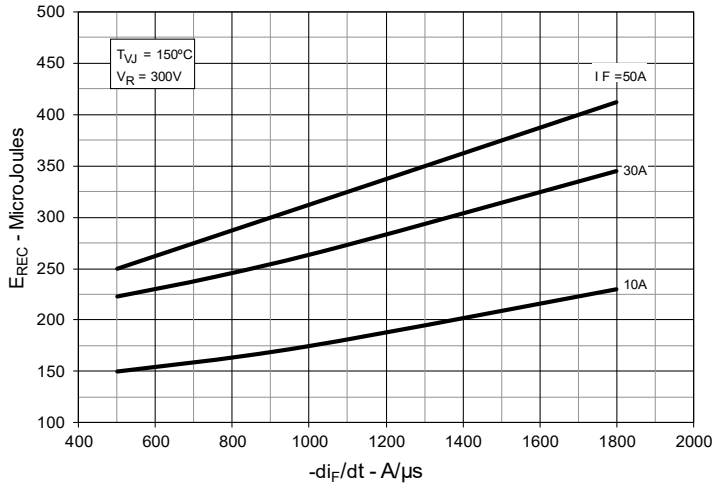
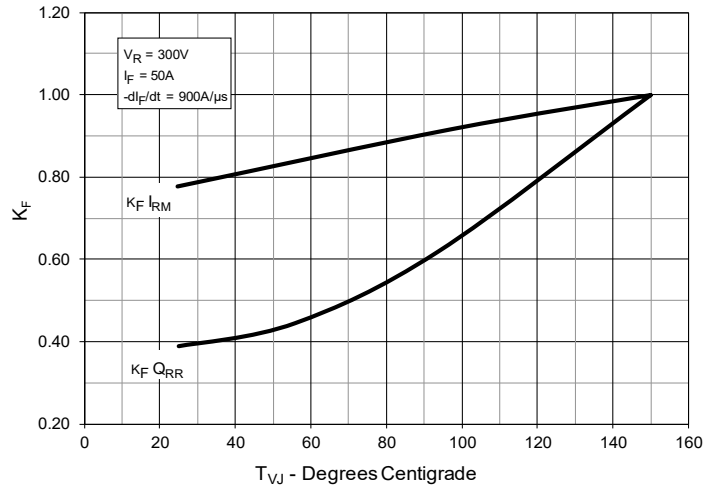
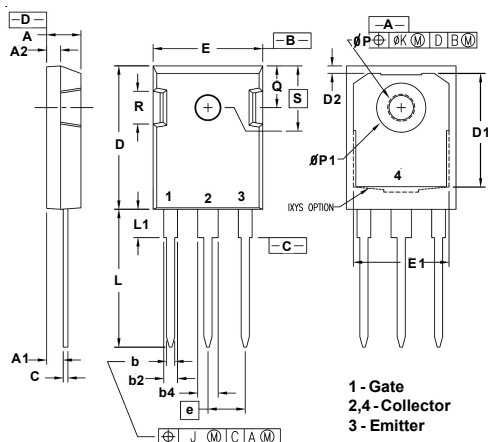


Fig. 27. Dynamic Parameters Q_{RR} , I_{RM} vs. Virtual Junction Temperature T_{VJ}



TO-247 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	



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